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P-Channel 100 V (D-S) MOSFET

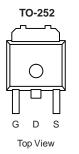
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) I _D (A)		Q _g (Typ.)	
- 100	0.08 at V _{GS} = - 10 V	- 25	17.9	
	0.09 at V _{GS} = - 4.5 V	- 20	17.9	

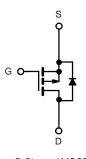
FEATURES

- DT-Trench Power MOSFET
- + 100 % $\rm R_g$ and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Power Switch
- DC/DC Converters





P-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S $T_C = 25 \degree C$, unless othe	rwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 100	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	- 25		
	T _C = 70 °C		- 17.3		
Pulsed Drain Current		I _{DM}	- 75	A	
Avalanche Current		I _{AS}	- 20		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	19.2	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	D	37.1 ^b	w	
	T _A = 25 °C ^c	P _D	2.9		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	2.9	0/11	

Notes:

a. Duty cycle ≤ 1 %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).



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SPECIFICATIONS $T_J = 25^{\circ}$ Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	• • • • • •			.,,,,,,		
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} = 0 V, I _D = - 250 μA	- 100			- v
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1		- 3	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA
Zero Gate Voltage Drain Current	IDSS	V _{DS} = - 100 V, V _{GS} = 0 V			- 1	μΑ
		V _{DS} = - 100 V, V _{GS} = 0 V, T _J = 125 °C			- 50	
		V _{DS} = - 100 V, V _{GS} = 0 V, T _J = 150 °C			- 250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 10 V, V_{GS} = - 10 V	- 15			А
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 3.6 A		0.08	0.09	Ω
		V _{GS} = - 4.5 V, I _D = - 3.4 A		0.09	0.10	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 3.6 A		16		S
Dynamic ^b	I			I		
Input Capacitance	C _{iss}			1043		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 50 V, f = 1 MHz		65		
Reverse Transfer Capacitance	C _{rss}	1		41		
Total Gate Charge ^c	Qg	$V_{DS} = -50 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.6 \text{ A}$		23.2	34.8	nC
		V _{DS} = - 50 V, V _{GS} = - 4.5 V, I _D = - 3.6 A		11.7	17.9	
Gate-Source Charge ^c	Q _{gs}			3.5		
Gate-Drain Charge ^c	Q _{gd}			4.8		
Gate Resistance	Rg	f = 1 MHz	1.2	5.7	11.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			7	14	
Rise Time ^c	t _r	$V_{DD} = -50 \text{ V}, \text{ R}_{L} = 17.2 \Omega$ $I_{D} \cong -2.9 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{g} = 1 \Omega$		12	18	ns
Turn-Off Delay Time ^c	t _{d(off)}			33	50	
Fall Time ^c	t _f			9	18	
Drain-Source Body Diode Ratings an	nd Characteri	istics T _C = 25 °C ^b				
Continuous Current	۱ _S				- 20	٨
Pulsed Current	I _{SM}				- 75	A
Forward Voltage ^a	V _{SD}	I _F = - 2.9 A, V _{GS} = 0 V		- 0.8	- 1.5	V
Reverse Recovery Time	t _{rr}			50	75	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 2.9 A, dl/dt = 100 A/μs		- 4	- 6	А
Reverse Recovery Charge	Q _{rr}	1		98	147	nC

Notes:

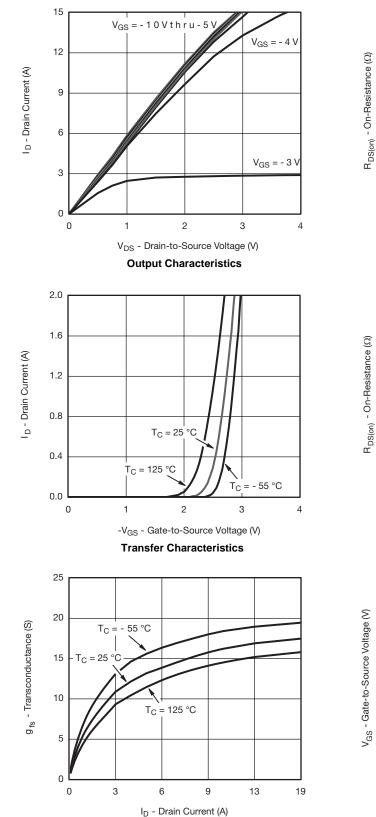
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

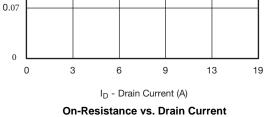
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 $V_{GS} = -10 V$



Transconductance

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

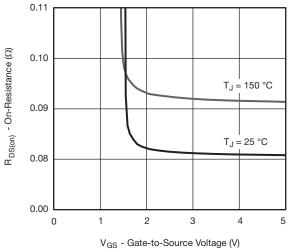


 $V_{GS} = -4.5$ V

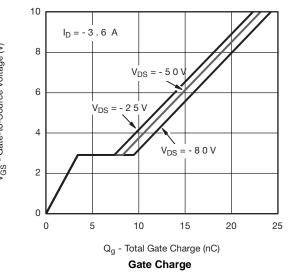
0.13

0.11

0.09

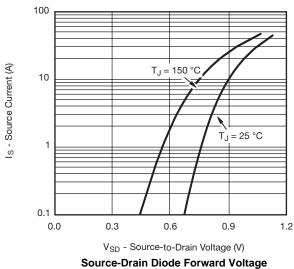


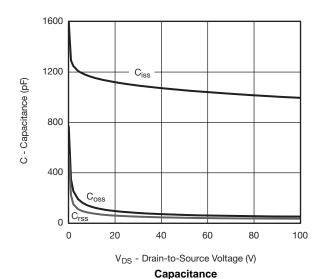
On-Resistance vs. Gate-to-Source Voltage

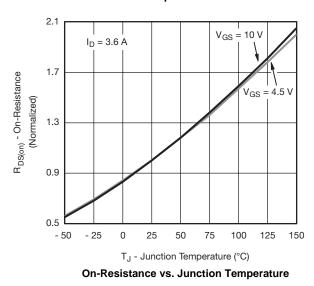


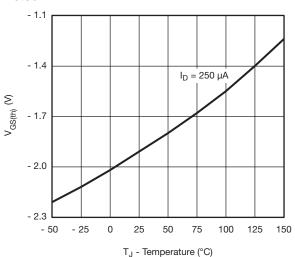
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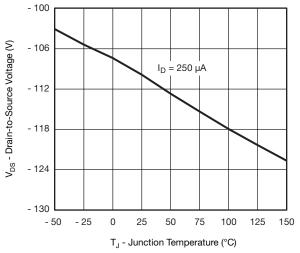




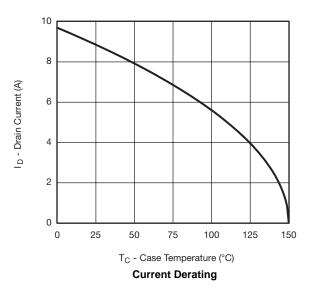




Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



0.2

0.1 0.05

0.1 10-4

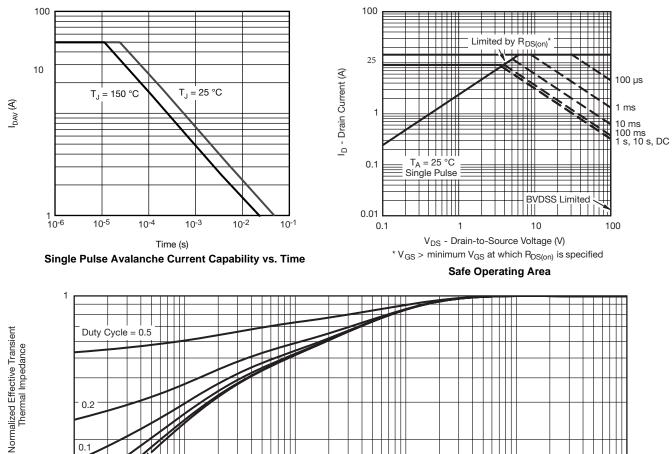
02 0. 111 Single Pulse

10⁻³

DTU25P10

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10-2

10-1

Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

1

10

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